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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

	Bailey et al.	Docket No.:	TI-27935
Serial No.:	09/452,691	Examiner:	Fenty, J.
Filed:	12/02/99	Art Unit:	2815

For: AN INTEGRATED CIRCUIT HAVING A THIN FILM RESISTOR LOCATED WITHIN A MULTILEVEL DIELECTRIC BETWEEN AN UPPER AND LOWER METAL INTERCONNECT LAYER

Amendment under 37 CFR 1.111

Assistant Commissioner of Patents
Washington, DC 20231

Dear Sir:

The following amendments and remarks are offered in response to the Examiner's Office Action dated 10/03/2002. They are respectfully submitted as a full and complete response to that Action.

Please amend the above-referenced application as follows:

In the Claims:

Amend claim 1 to read as follows:

1. (twice amended) An integrated circuit comprising:

a lower metal interconnect layer located over a semiconductor body;

a multi-level dielectric layer located over said lower interconnect layer;

an upper metal interconnect layer located over said multi-level dielectric layer; and

a thin film resistor embedded within said multi-level dielectric layer between said low r m tal interconnect layer and said upper metal interconn ct

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